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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100leafb-50

Table 1-1. List of Ordering Part Numbers

(12/12)

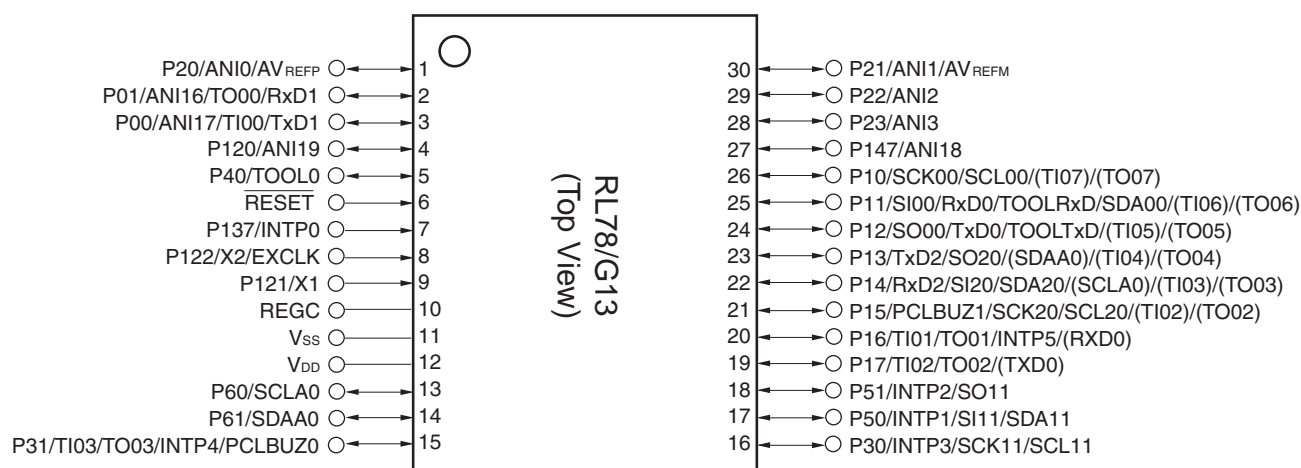
Pin count	Package	Data flash	Fields of Application ^{Note}	Ordering Part Number
128 pins	128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)	Mounted	A	R5F100SHAFB#V0, R5F100SJAFB#V0, R5F100SKAFB#V0, R5F100SLAFB#V0 R5F100SHAFB#X0, R5F100SJAFB#X0, R5F100SKAFB#X0, R5F100SLAFB#X0
			D	R5F100SHDFB#V0, R5F100SJDFB#V0, R5F100SKDFB#V0, R5F100SLDFB#V0 R5F100SHDFB#X0, R5F100SJDFB#X0, R5F100SKDFB#X0, R5F100SLDFB#X0
		Not mounted	A	R5F101SHAFB#V0, R5F101SJAFB#V0, R5F101SKAFB#V0, R5F101SLAFB#V0 R5F101SHAFB#X0, R5F101SJAFB#X0, R5F101SKAFB#X0, R5F101SLAFB#X0
			D	R5F101SHDFB#V0, R5F101SJDFB#V0, R5F101SKDFB#V0, R5F101SLDFB#V0 R5F101SHDFB#X0, R5F101SJDFB#X0, R5F101SKDFB#X0, R5F101SLDFB#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.4 30-pin products

- 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



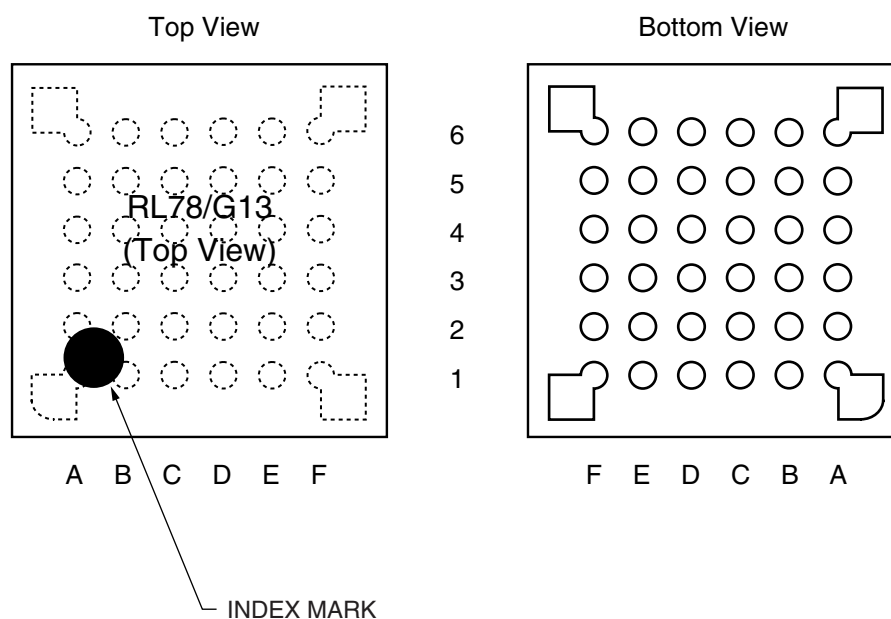
Caution Connect the REGC pin to V_{ss} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.3.6 36-pin products

- 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



	A	B	C	D	E	F	
6	P60/SCLA0	V _{DD}	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	6
5	P62	P61/SDAA0	V _{SS}	REGC	RESET	P120/ANI19	5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/(SCLA0) /(TI03)/(TO03)	P31/TI03/TO03/ INTP4/ PCLBUZ0	P00/TI00/TxD1	P01/TO00/RxD1	4
3	P50/INTP1/ SI11/SDA11	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ (TI02)/(TO02)	P22/ANI2	P20/ANI0/ AV _{REFP}	P21/ANI1/ AV _{REFM}	3
2	P30/INTP3/ SCK11/SCL11	P16/TI01/TO01/ INTP5/(RxD0)	P12/SO00/ TxD0/TOOLTxD /(TI05)/(TO05)	P11/SI00/RxD0/ TOOLRxD/ SDA00/(TI06)/ (TO06)	P24/ANI4	P23/ANI3	2
1	P51/INTP2/ SO11	P17/TI02/TO02/ (TxD0)	P13/TxD2/ SO20/(SDAA0)/ (TI04)/(TO04)	P10/SCK00/ SCL00/(TI07)/ (TO07)	P147/ANI18	P25/ANI5	1
	A	B	C	D	E	F	

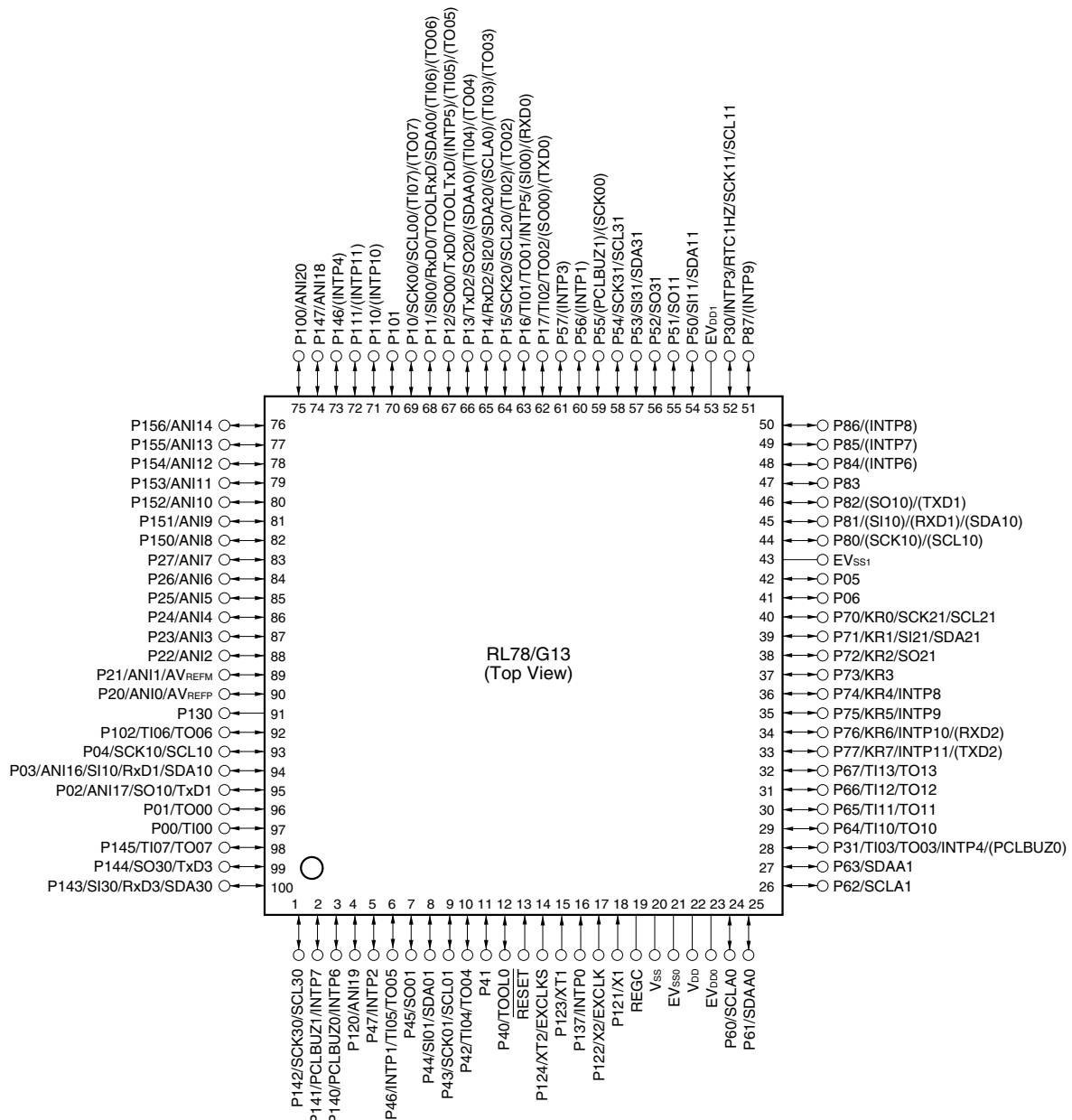
Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.3.13 100-pin products

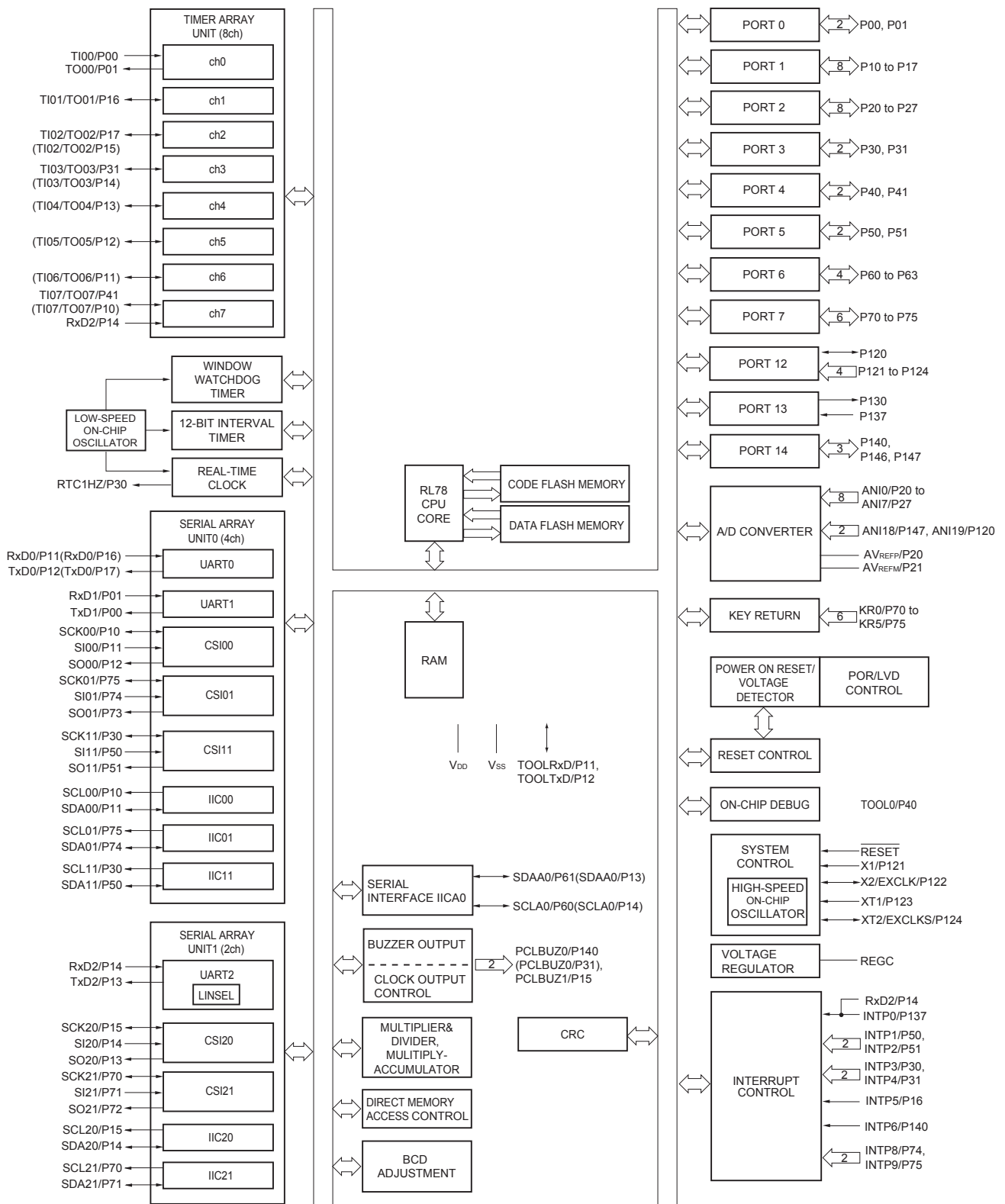
- 100-pin plastic LQFP (14 × 14 mm, 0.5 mm pitch)



- Cautions**
1. Make EV_{SS0}, EV_{SS1} pins the same potential as V_{SS} pin.
 2. Make V_{DD} pin the potential that is higher than EV_{DD0}, EV_{DD1} pins (EV_{DD0} = EV_{DD1}).
 3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

- Remarks**
1. For pin identification, see 1.4 Pin Identification.
 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the V_{SS}, EV_{SS0} and EV_{SS1} pins to separate ground lines.
 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.9 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products**(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	HS (high-speed main) mode Note 5	f _{IH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.3		mA
						V _{DD} = 3.0 V		2.3		mA
					Normal operation	V _{DD} = 5.0 V		5.2	8.5	mA
						V _{DD} = 3.0 V		5.2	8.5	mA
				f _{IH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.1	6.6	mA
						V _{DD} = 3.0 V		4.1	6.6	mA
				f _{IH} = 16 MHz Note 3	Normal operation	V _{DD} = 5.0 V		3.0	4.7	mA
						V _{DD} = 3.0 V		3.0	4.7	mA
			LS (low-speed main) mode Note 5	f _{IH} = 8 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.3	2.1	mA
						V _{DD} = 2.0 V		1.3	2.1	mA
			LV (low-voltage main) mode Note 5	f _{IH} = 4 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.3	1.8	mA
						V _{DD} = 2.0 V		1.3	1.8	mA
			HS (high-speed main) mode Note 5	f _{MX} = 20 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		3.4	5.5	mA
						Resonator connection		3.6	5.7	mA
				f _{MX} = 20 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		3.4	5.5	mA
						Resonator connection		3.6	5.7	mA
				f _{MX} = 10 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		2.1	3.2	mA
						Resonator connection		2.1	3.2	mA
				f _{MX} = 10 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		2.1	3.2	mA
						Resonator connection		2.1	3.2	mA
			LS (low-speed main) mode Note 5	f _{MX} = 8 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		1.2	2.0	mA
						Resonator connection		1.2	2.0	mA
				f _{MX} = 8 MHz Note 2, V _{DD} = 2.0 V	Normal operation	Square wave input		1.2	2.0	mA
						Resonator connection		1.2	2.0	mA
			Subsystem clock operation	f _{SUB} = 32.768 kHz Note 4 T _A = -40°C	Normal operation	Square wave input		4.8	5.9	μA
						Resonator connection		4.9	6.0	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +25°C	Normal operation	Square wave input		4.9	5.9	μA
						Resonator connection		5.0	6.0	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +50°C	Normal operation	Square wave input		5.0	7.6	μA
						Resonator connection		5.1	7.7	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +70°C	Normal operation	Square wave input		5.2	9.3	μA
						Resonator connection		5.3	9.4	μA
				f _{SUB} = 32.768 kHz Note 4 T _A = +85°C	Normal operation	Square wave input		5.7	13.3	μA
						Resonator connection		5.8	13.4	μA

(Notes and Remarks are listed on the next page.)

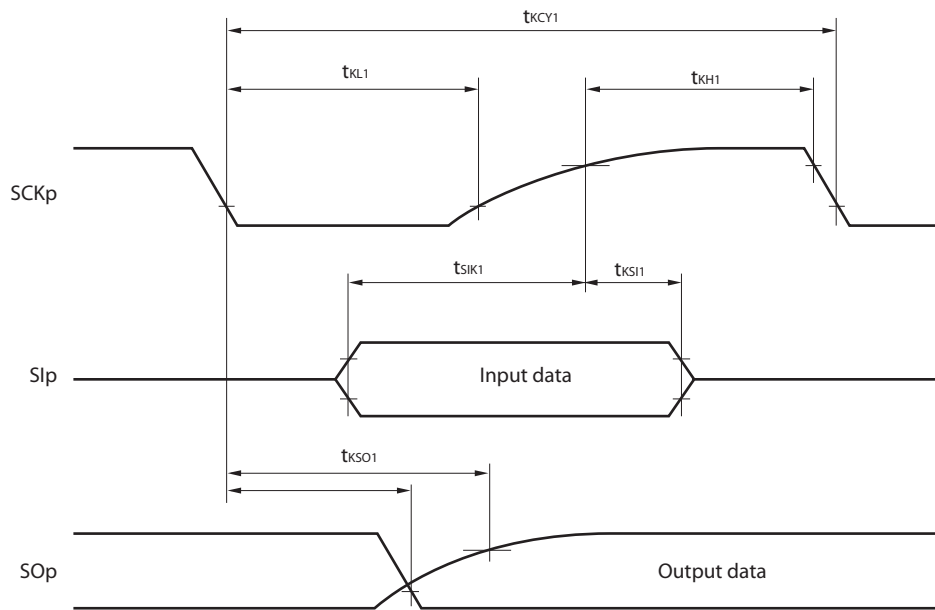
- Notes**
1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 3. When high-speed system clock and subsystem clock are stopped.
 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 32 MHz
 - $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 16 MHz
 - LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 8 MHz
 - LV (low-voltage main) mode: $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 4 MHz

- Remarks**
1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH}: High-speed on-chip oscillator clock frequency
 3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

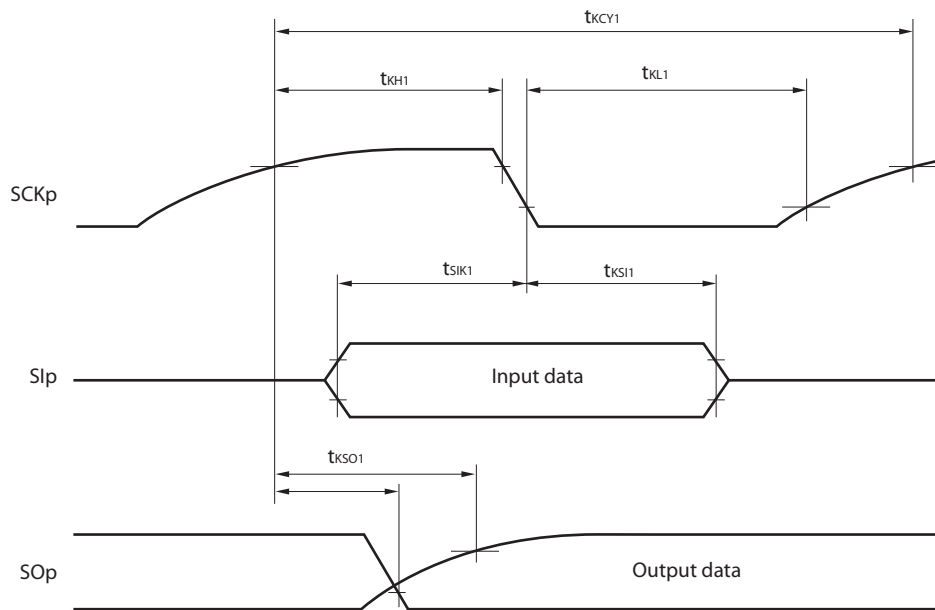
- Notes**
1. Total current flowing into V_{DD} , EV_{DD0} , and EV_{DD1} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} , and EV_{DD1} , or V_{SS} , EV_{SS0} , and EV_{SS1} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 32 MHz
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 16 MHz
 - LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 8 MHz
 - LV (low-voltage main) mode: $1.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$ @ 1 MHz to 4 MHz
 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks 1.** f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- 2.** f_{IH} : High-speed on-chip oscillator clock frequency
- 3.** f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
- 4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
- 2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

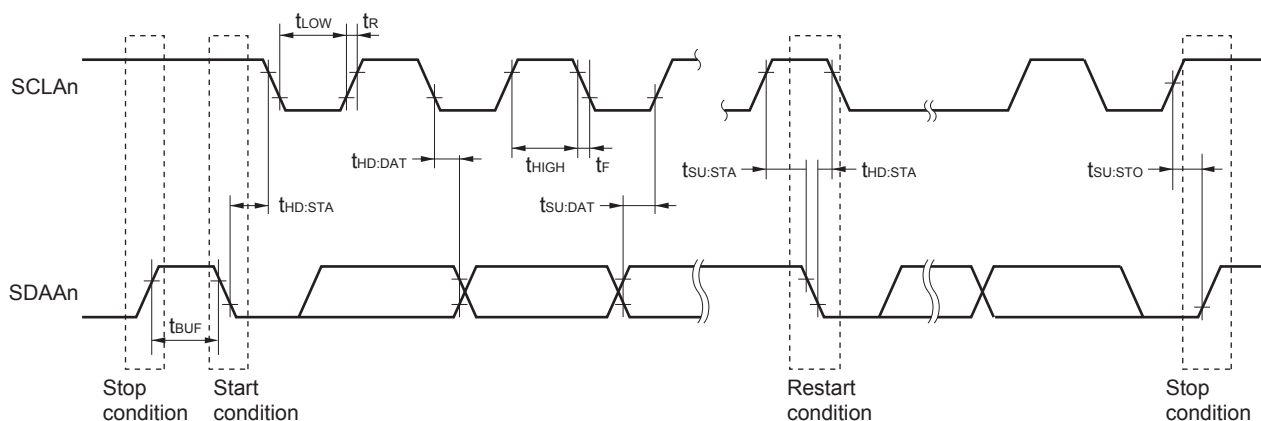
(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note 1}	t _{KCY2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	24 MHz < f _{MCK}	14/ f _{MCK}		—		—		ns
			20 MHz < f _{MCK} ≤ 24 MHz	12/ f _{MCK}		—		—		ns
			8 MHz < f _{MCK} ≤ 20 MHz	10/ f _{MCK}		—		—		ns
			4 MHz < f _{MCK} ≤ 8 MHz	8/f _{MCK}		16/ f _{MCK}		—		ns
			f _{MCK} ≤ 4 MHz	6/f _{MCK}		10/ f _{MCK}		10/ f _{MCK}		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	24 MHz < f _{MCK}	20/ f _{MCK}		—		—		ns
			20 MHz < f _{MCK} ≤ 24 MHz	16/ f _{MCK}		—		—		ns
			16 MHz < f _{MCK} ≤ 20 MHz	14/ f _{MCK}		—		—		ns
			8 MHz < f _{MCK} ≤ 16 MHz	12/ f _{MCK}		—		—		ns
			4 MHz < f _{MCK} ≤ 8 MHz	8/f _{MCK}		16/ f _{MCK}		—		ns
			f _{MCK} ≤ 4 MHz	6/f _{MCK}		10/ f _{MCK}		10/ f _{MCK}		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	24 MHz < f _{MCK}	48/ f _{MCK}		—		—		ns
			20 MHz < f _{MCK} ≤ 24 MHz	36/ f _{MCK}		—		—		ns
			16 MHz < f _{MCK} ≤ 20 MHz	32/ f _{MCK}		—		—		ns
			8 MHz < f _{MCK} ≤ 16 MHz	26/ f _{MCK}		—		—		ns
			4 MHz < f _{MCK} ≤ 8 MHz	16/ f _{MCK}		16/ f _{MCK}		—		ns
			f _{MCK} ≤ 4 MHz	10/ f _{MCK}		10/ f _{MCK}		10/ f _{MCK}		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(3) I²C fast mode plus(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Fast mode plus: f _{CLK} ≥ 10 MHz 2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	1000	—	—	—	—	kHz
Setup time of restart condition	t _{SU:STA}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0.26	—	—	—	—	—	μs
Hold time ^{Note 1}	t _{HD:STA}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0.26	—	—	—	—	—	μs
Hold time when SCLA0 = "L"	t _{LOW}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0.5	—	—	—	—	—	μs
Hold time when SCLA0 = "H"	t _{HIGH}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0.26	—	—	—	—	—	μs
Data setup time (reception)	t _{SU:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	50	—	—	—	—	—	μs
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	0.45	—	—	—	—	μs
Setup time of stop condition	t _{SU:STO}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0.26	—	—	—	—	—	μs
Bus-free time	t _{BUF}	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0.5	—	—	—	—	—	μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.<R> 2. The maximum value (MAX.) of t_{HD:DAT} is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.**Caution** The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.**Remark** The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.Fast mode plus: C_b = 120 pF, R_b = 1.1 kΩ**I²C serial transfer timing****Remark** n = 0, 1

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V <small>Note 3</small>		1.2	±10.5	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V _{DD} ≤ 5.5 V	57		95	μs
Conversion time	t _{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V <small>Note 3</small>			±0.85	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V <small>Note 3</small>			±0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V <small>Note 3</small>			±6.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V <small>Note 3</small>			±2.5	LSB
Analog input voltage	V _{AIN}	ANI0 to ANI14	0			V _{DD}	V
		ANI16 to ANI26	0			EV _{DD0}	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{BGR} ^{Note 4}				V
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{TMPS25} ^{Note 4}				V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$) (5/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit		
Input leakage current, high	I _{LH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V _I = EV _{DD0}		1	μA		
	I _{LH2}	P20 to P27, P137, P150 to P156, RESET	V _I = V _{DD}		1	μA		
	I _{LH3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V _I = V _{DD}	In input port or external clock input	1	μA		
				In resonator connection	10	μA		
Input leakage current, low	I _{LIL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V _I = EV _{SS0}		−1	μA		
	I _{LIL2}	P20 to P27, P137, P150 to P156, RESET	V _I = V _{SS}		−1	μA		
	I _{LIL3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V _I = V _{SS}	In input port or external clock input	−1	μA		
				In resonator connection	−10	μA		
On-chip pll-up resistance	R _U	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V _I = EV _{SS0} , In input port		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes**
1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.

- Remarks**
1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH} : High-speed on-chip oscillator clock frequency
 3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

(4) During communication at same potential (simplified I²C mode)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		400 ^{Note1}	kHz
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$		100 ^{Note1}	
Hold time when SCLr = "L"	t_{LOW}	$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1200		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	4600		ns
Hold time when SCLr = "H"	t_{HIGH}	$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1200		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	4600		ns
Data setup time (reception)	$t_{\text{SU:DAT}}$	$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 220$ ^{Note2}		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	$1/f_{\text{MCK}} + 580$ ^{Note2}		ns
Data hold time (transmission)	$t_{\text{HD:DAT}}$	$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	0	1420	ns

Notes 1. The value must also be equal to or less than $f_{\text{MCK}}/4$.2. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{\text{KCY1}} \geq 4/f_{\text{CLK}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	600		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	1000		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	2300		ns
SCKp high-level width	t_{KH1}		$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 150$		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 340$		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 916$		ns
SCKp low-level width	t_{KL1}		$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 24$		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 36$		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 100$		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to $+105^{\circ}\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time ^{Note 1}	t _{KCY2}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$	$24\text{ MHz} < f_{\text{MCK}}$	$28/f_{\text{MCK}}$		ns
			$20\text{ MHz} < f_{\text{MCK}} \leq 24\text{ MHz}$	$24/f_{\text{MCK}}$		ns
			$8\text{ MHz} < f_{\text{MCK}} \leq 20\text{ MHz}$	$20/f_{\text{MCK}}$		ns
			$4\text{ MHz} < f_{\text{MCK}} \leq 8\text{ MHz}$	$16/f_{\text{MCK}}$		ns
			$f_{\text{MCK}} \leq 4\text{ MHz}$	$12/f_{\text{MCK}}$		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$	$24\text{ MHz} < f_{\text{MCK}}$	$40/f_{\text{MCK}}$		ns
			$20\text{ MHz} < f_{\text{MCK}} \leq 24\text{ MHz}$	$32/f_{\text{MCK}}$		ns
			$16\text{ MHz} < f_{\text{MCK}} \leq 20\text{ MHz}$	$28/f_{\text{MCK}}$		ns
			$8\text{ MHz} < f_{\text{MCK}} \leq 16\text{ MHz}$	$24/f_{\text{MCK}}$		ns
			$4\text{ MHz} < f_{\text{MCK}} \leq 8\text{ MHz}$	$16/f_{\text{MCK}}$		ns
			$f_{\text{MCK}} \leq 4\text{ MHz}$	$12/f_{\text{MCK}}$		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$	$24\text{ MHz} < f_{\text{MCK}}$	$96/f_{\text{MCK}}$		ns
			$20\text{ MHz} < f_{\text{MCK}} \leq 24\text{ MHz}$	$72/f_{\text{MCK}}$		ns
			$16\text{ MHz} < f_{\text{MCK}} \leq 20\text{ MHz}$	$64/f_{\text{MCK}}$		ns
			$8\text{ MHz} < f_{\text{MCK}} \leq 16\text{ MHz}$	$52/f_{\text{MCK}}$		ns
			$4\text{ MHz} < f_{\text{MCK}} \leq 8\text{ MHz}$	$32/f_{\text{MCK}}$		ns
			$f_{\text{MCK}} \leq 4\text{ MHz}$	$20/f_{\text{MCK}}$		ns
SCKp high-/low-level width	t _{KH2} , t _{KL2}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$		$t_{\text{KCY2}}/2 - 24$		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$		$t_{\text{KCY2}}/2 - 36$		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$ ^{Note 2}		$t_{\text{KCY2}}/2 - 100$		ns
Slp setup time (to SCKp↑) ^{Note 2}	t _{SIK2}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$		$1/f_{\text{MCK}} + 40$		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$		$1/f_{\text{MCK}} + 40$		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$		$1/f_{\text{MCK}} + 60$		ns
Slp hold time (from SCKp↑) ^{Note 3}	t _{KSI2}			$1/f_{\text{MCK}} + 62$		ns
Delay time from SCKp↓ to SOp output ^{Note 4}	t _{KSO2}	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 1.4\text{ k}\Omega$			$2/f_{\text{MCK}} + 240$	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 2.7\text{ k}\Omega$			$2/f_{\text{MCK}} + 428$	ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $C_b = 30\text{ pF}$, $R_b = 5.5\text{ k}\Omega$			$2/f_{\text{MCK}} + 1146$	ns

(Notes, Caution and Remarks are listed on the next page.)

(2) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (–) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin : ANI16 to ANI26

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (–) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$	1.2	± 5.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin : ANI16 to ANI26	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
Zero-scale error ^{Notes 1, 2}	E_{ZS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.35	%FSR
Full-scale error ^{Notes 1, 2}	E_{FS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 2.0	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI26	0		AV_{REFP} and EV_{DD0}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. When $AV_{REFP} < EV_{DD0} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

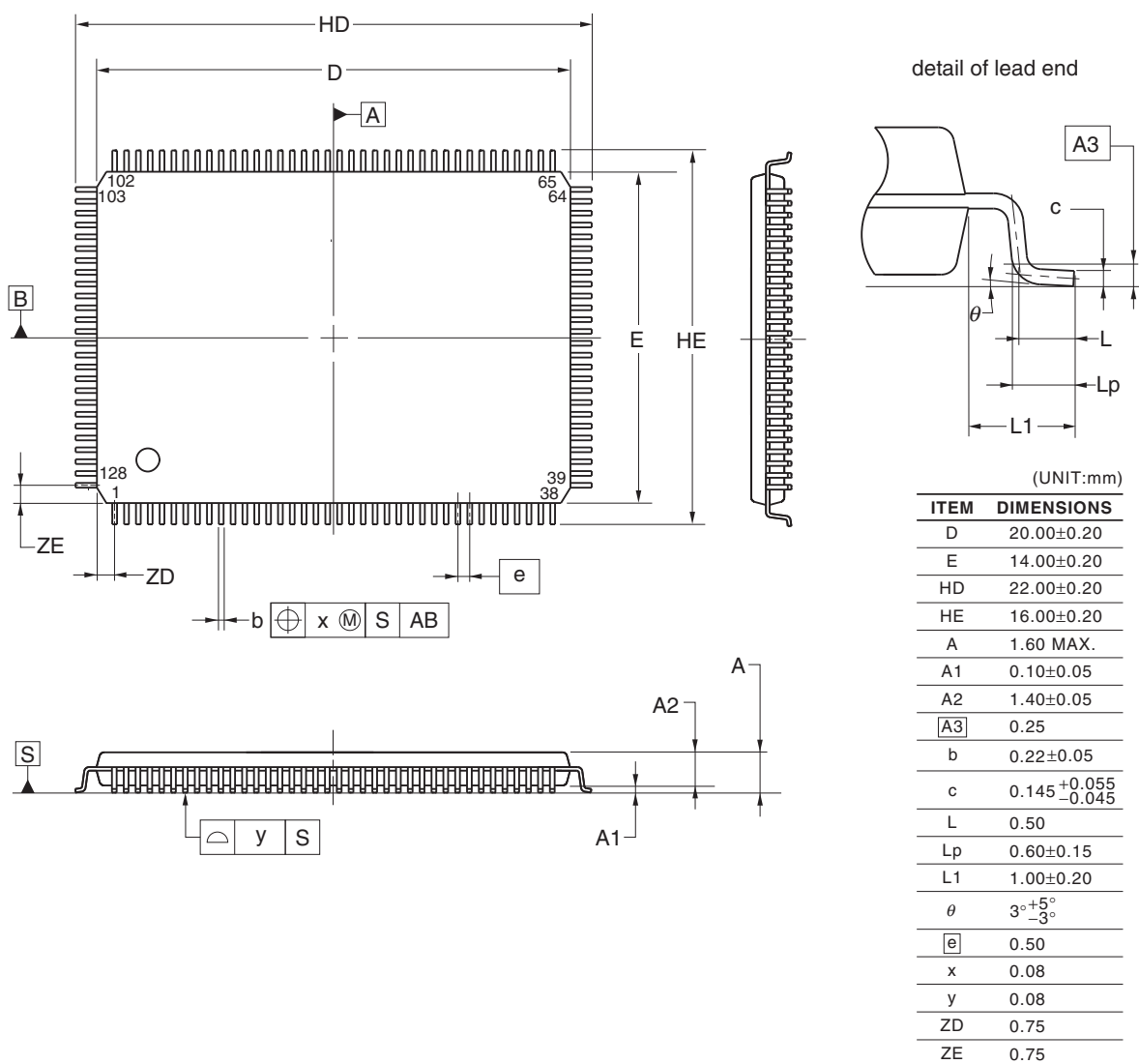
Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4.14 128-pin Products

R5F100SHAFB, R5F100SJAFB, R5F100SKAFB, R5F100SLAFB
 R5F101SHAFB, R5F101SJAFB, R5F101SKAFB, R5F101SLAFB
 R5F100SHDFB, R5F100SJDFB, R5F100SKDFB, R5F100SLDFB
 R5F101SHDFB, R5F101SJDFB, R5F101SKDFB, R5F101SLDFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP128-14x20-0.50	PLQP0128KD-A	P128GF-50-GBP-1	0.92



Revision History	RL78/G13 Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Feb 29, 2012	-	First Edition issued
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count corrected.
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.
		59, 63, 67	Descriptions of Note 8 in a table corrected.
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.
3.00	Aug 02, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution
		16 to 32	Modification of package type in 1.3.1 to 1.3.14
		33	Modification of description in 1.4 Pin Identification
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions
		55	Modification of description in table of Absolute Maximum Ratings ($T_A = 25^{\circ}\text{C}$)
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics
		57	Modification of table in 2.2.2 On-chip oscillator characteristics
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products
		68	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		70	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products
		72	Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products
		75	Modification of (4) Peripheral Functions (Common to all products)
		77	Modification of table in 2.4 AC Characteristics
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		80	Modification of figures of AC Timing Test Points and External System Clock Timing